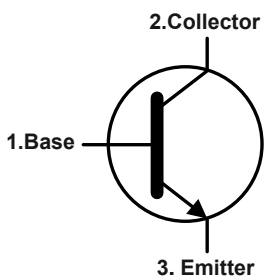


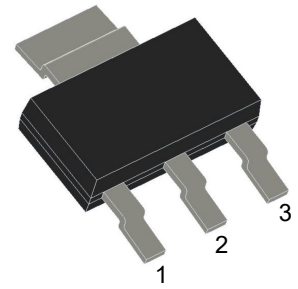
### Features

- For AF driver and output stages
- High collector current
- Low collector-emitter saturation voltage

### Equivalent Circuit

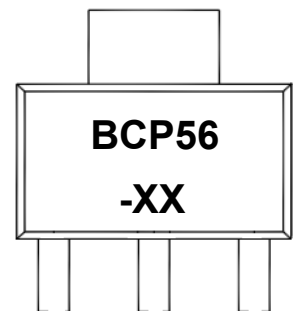


### SOT-223



1.Base 2.Collector 3. Emitter

### Marking Code :



Note: The "X" is variable  
 BCP56ST-10=BCP56 -10  
 BCP56ST-16=BCP56 -16

### Absolute Maximum Ratings

Ratings at 25°C ambient temperature unless otherwise specified.

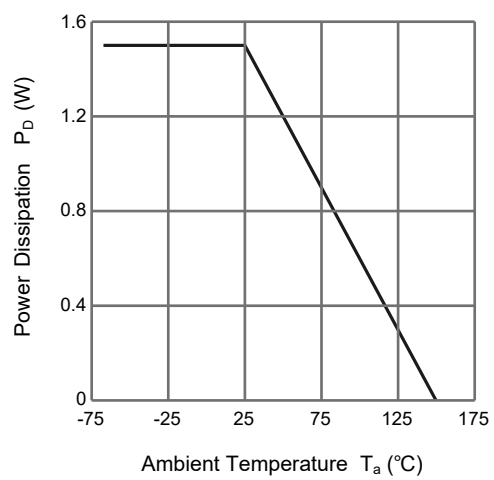
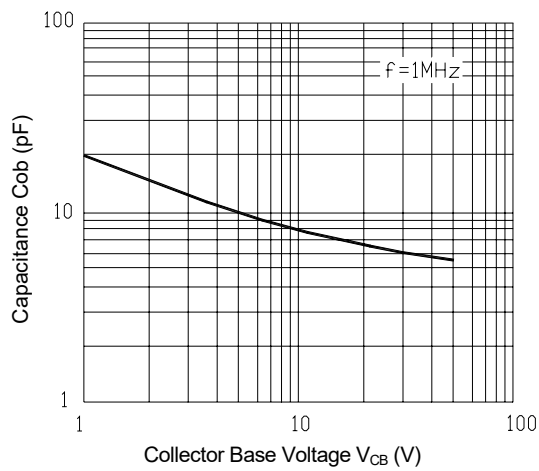
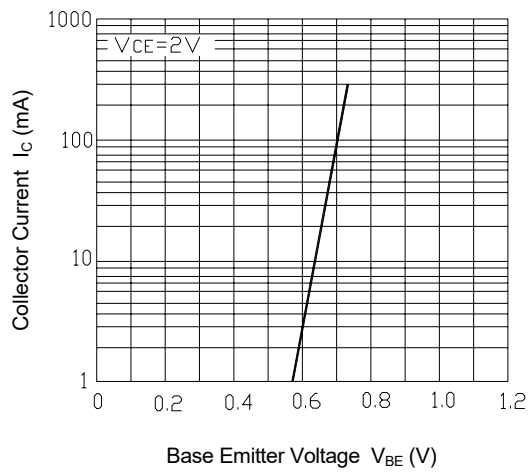
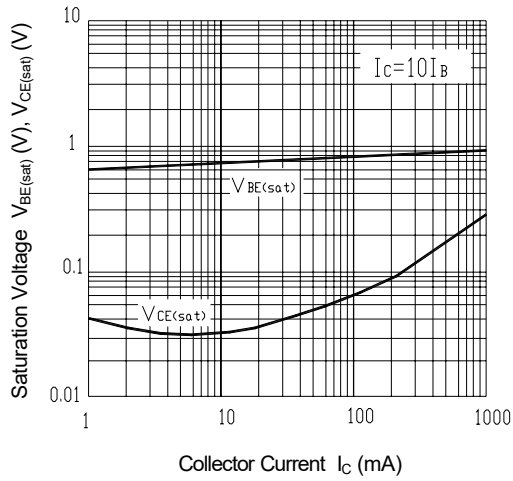
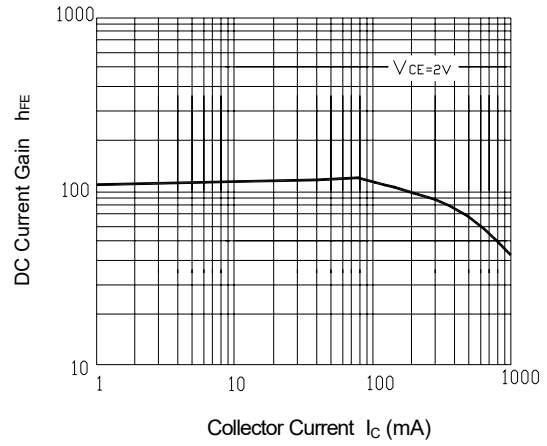
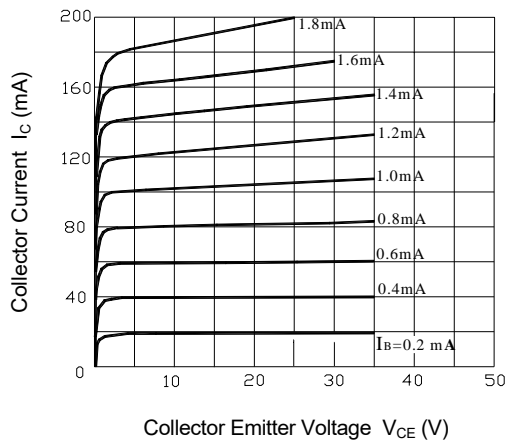
Parameter	Symbol	Value	Unit
Collector Base Voltage	$V_{CBO}$	100	V
Collector Emitter Voltage	$V_{CEO}$	80	V
Emitter Base Voltage	$V_{EBO}$	5	V
Collector Current	$I_C$	1	A
Peak Collector Current	$I_{CM}$	1.5	A
Maximum Power Dissipation	$P_D$	1.5	W
Junction Temperature	$T_J$	150	°C
Storage Temperature Range	$T_{STG}$	-55 to +150	°C



### Electrical Characteristics (T<sub>A</sub>=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at V <sub>CE</sub> = 2 V, I <sub>C</sub> = 5 mA at V <sub>CE</sub> = 2 V, I <sub>C</sub> = 150 mA    Gain Group at V <sub>CE</sub> = 2 V, I <sub>C</sub> = 500 mA	-10 H <sub>FE</sub> -16	40 63 100 25	-- -- -- --	-- 160 250 --	--
Collector Base Cutoff Current at V <sub>CB</sub> = 30V	I <sub>CBO</sub>	--	--	100	nA
Emitter Base Cutoff Current at V <sub>EB</sub> = 5 V	I <sub>EBO</sub>	--	--	100	nA
Collector Base Breakdown Voltage at I <sub>C</sub> = 100 μA	V <sub>(BR)CBO</sub>	100	--	--	V
Collector Emitter Breakdown Voltage at I <sub>C</sub> = 1 mA	V <sub>(BR)CEO</sub>	80	--	--	V
Emitter Base Breakdown Voltage at I <sub>E</sub> = 100 μA	V <sub>(BR)EBO</sub>	5	--	--	V
Collector Emitter Saturation Voltage at I <sub>C</sub> = 500 mA, I <sub>B</sub> = 50 mA	V <sub>CE(sat)</sub>	--	--	0.5	V
Base Emitter On Voltage at V <sub>CE</sub> = 2 V, I <sub>C</sub> = 500 mA	V <sub>BE(on)</sub>	--	--	1	V
Transition Frequency at V <sub>CE</sub> = 5 V, I <sub>C</sub> = 50 mA, f = 100 MHz	f <sub>T</sub>	100	--	--	MHz
Output Capacitance at V <sub>CB</sub> = 10 V, f = 1 MHz	C <sub>ob</sub>	--	6	--	pF

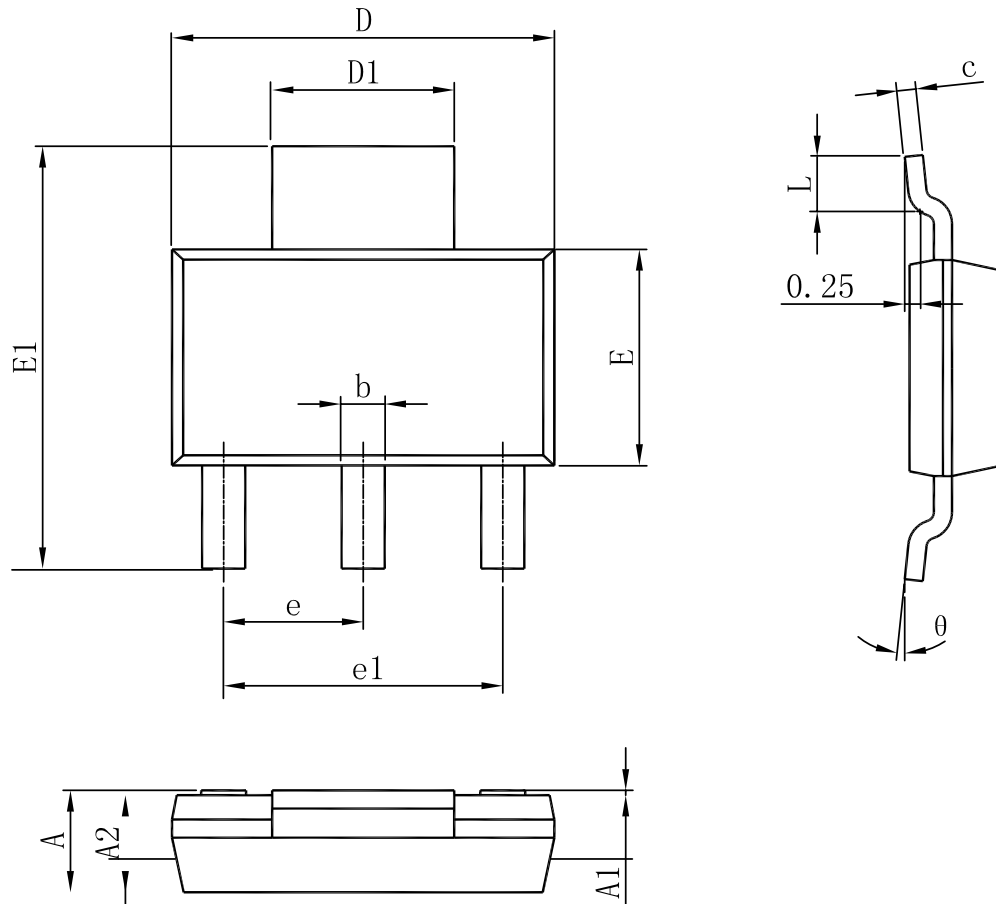
### Typical Characteristic Curves



### Package Outline

SOT-223

Dimensions in mm



1. 塑脂体无缺损、缩孔、气泡、裂纹等缺陷；
2. 树脂体上下部XY方向偏差、树脂体中心与引线框中心错位  $\pm 0.035$  ；
3. 粗糙度Ra为0.4--0.6。

Symbol	Dimensions In Millimeters		
	MIN	NOM	MAX
A	/	/	1.80
A1	0.02	/	0.10
A2	1.50	1.60	1.70
b	0.66	0.71	0.84
c	0.23	0.30	0.35
D	6.30	6.50	6.70
D1	2.90	3.00	3.10
E	3.30	3.50	3.70
E1	6.70	7.00	7.30
e	2.30 BASIC		
e1	4.60 BASIC		
L	0.75	/	/
$\theta$	0°	/	10°

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